

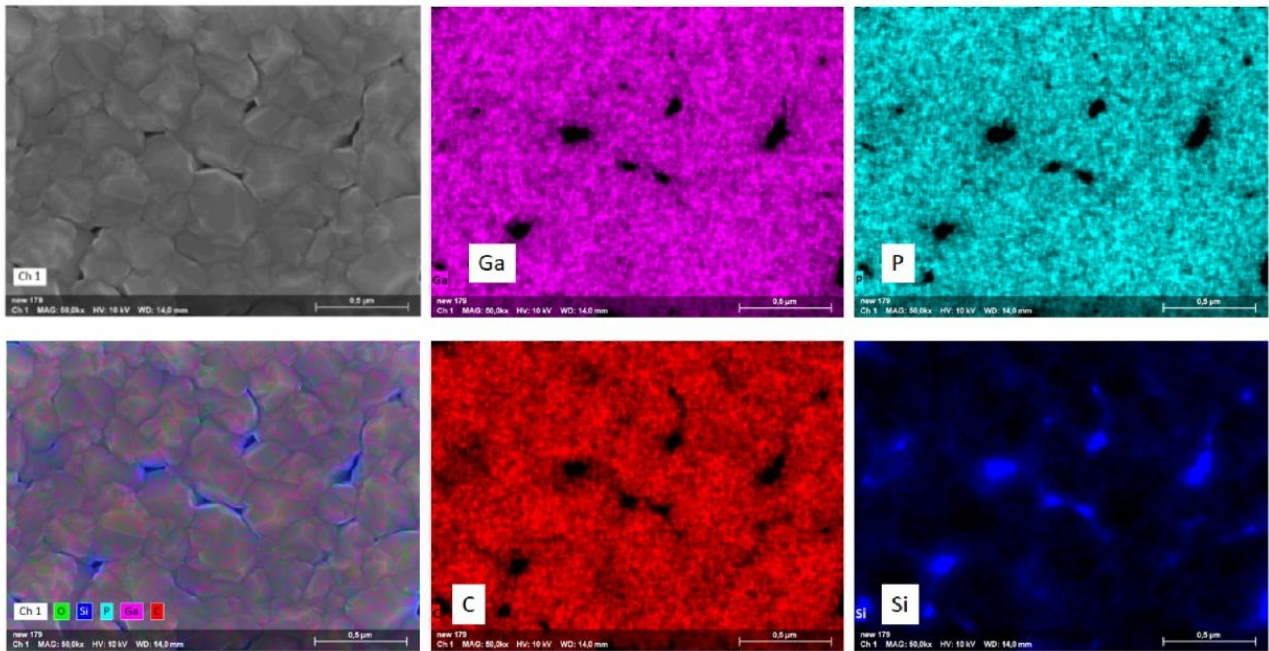
Customized epitaxy (III-V) GaP layers on Si

samples for tests, \$500 per sample (shipment included)

GaP on Si substrate

- Substrate: 2" Si, Type / Ori.: N / <100> / 4 deg off, Resistivity 1-10 Ohm.cm, 500 μ m \pm 25
- Thickness: 40nm-250nm
- Thickness uniformity within 80% of the wafer radius: \pm 15%

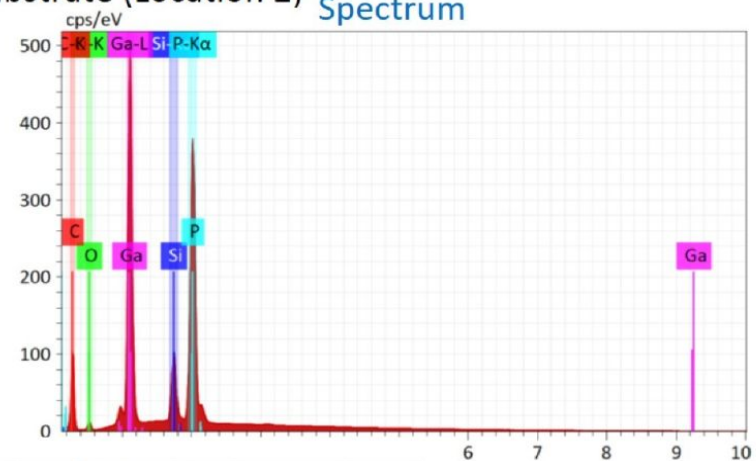
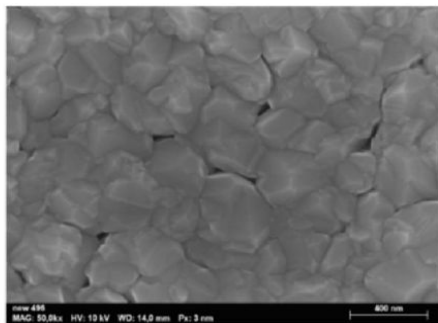
Elemental mapping (Location 2)



EDS of GaP thin films on Si substrate (Location 2)

SEM

Spectrum



Mass percentage of different element

Element	At. No.	Net	Mass [%]	Mass Norm. [%]	Atom [%]	abs. error [mass%] (1 σ)	rel. error [%] (1 σ)
Gallium	31	3894380	65,30	57,00	28,15	2,61	4,00
Phosphorus	15	3361240	18,88	16,48	18,32	0,37	1,97
Oxygen	8	68346	25,99	22,69	48,84	0,93	3,57
Silicon	14	720819	4,38	3,83	4,69	0,10	2,30
Sum			114,55	100,00	100,00		